

KSC2710

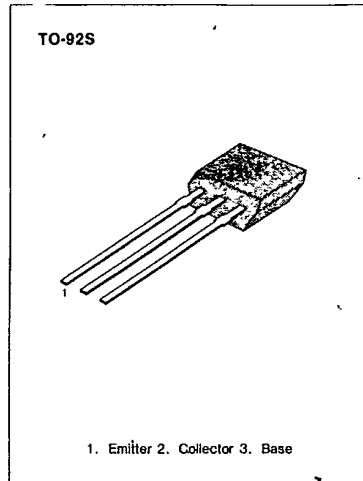
NPN EPITAXIAL SILICON TRANSISTOR

LOW FREQUENCY POWER AMPLIFIER

- Complement to KSA1150
- Collector Dissipation $P_C=300mW$

ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ C$)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	40	V
Collector-Emitter Voltage	V_{CEO}	20	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	500	mA
Collector Dissipation	P_C	300	mW
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature	T_{stg}	-55 ~ 150	$^\circ C$



ELECTRICAL CHARACTERISTICS ($T_a=25^\circ C$)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	$I_C=100\mu A, I_E=0$	40			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C=10mA, I_B=0$	20			V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E=-100\mu A, I_C=0$	5			V
Collector Cut-off Current	I_{CBO}	$V_{CB}=25V, I_E=0$			0.1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=3V, I_C=0$			0.1	μA
DC Current Gain	h_{FE}	$V_{CE}=1V, I_C=0.1A$	40		400	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=0.5A, I_B=0.05A$		0.18	0.4	V

h_{FE} CLASSIFICATION

Classification	R	O	Y	G
h_{FE}	40-80	70-140	120-240	200-400

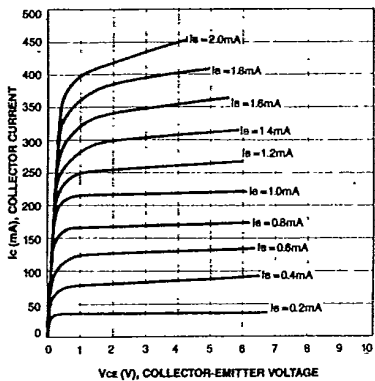
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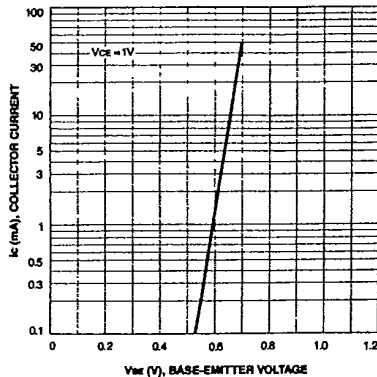
NPN EPITAXIAL SILICON TRANSISTOR

T-29-17

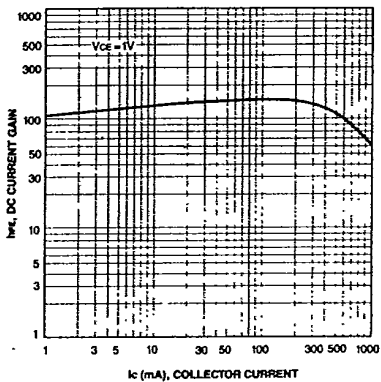
STATIC CHARACTERISTIC



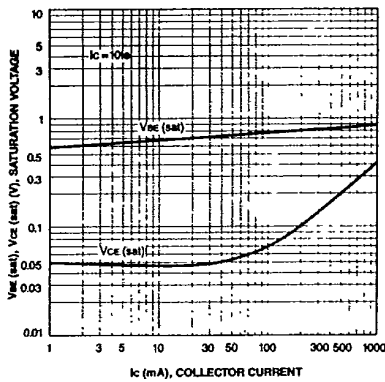
BASE-EMITTER ON VOLTAGE



DC CURRENT GAIN



**BASE-EMITTER SATURATION VOLTAGE
COLLECTOR-EMITTER SATURATION VOLTAGE**



COLLECTOR OUTPUT CAPACITANCE

